

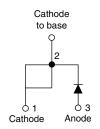
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Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 16 A



TO-247AC modified



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub> 16 A						
$V_{R}$	1200 V					
V <sub>F</sub> at I <sub>F</sub>	2.3 V					
t <sub>rr</sub> typ.	30 ns					
T <sub>J</sub> max.	150 °C					
Package	TO-247AC modified (2 pins)					
Circuit configuration	Single					

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test







FREE

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA16PB120HN3 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16PB120HN3 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PB120HN3 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	$V_R$		1200	V			
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	16				
Single pulse forward current	I <sub>FSM</sub>		190	А			
Maximum repetitive forward current	I <sub>FRM</sub>		64				
Maximum naugy dispination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	151	- w			
Maximum power dissipation		T <sub>C</sub> = 100 °C	60				
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C			

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	$V_{BR}$	Ι <sub>R</sub> = 100 μΑ		1200	ı	ı			
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 16 A	See fig. 1	-	2.5	3.0	V		
		I <sub>F</sub> = 32 A		-	3.2	3.93			
		I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C		-	2.3	2.7			
Maximum reverse leakage	I <sub>RM</sub>	$V_R = V_R$ rated	Coo fig. 0	-	0.75	20	μΑ		
current		$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	See fig. 2	-	375	2000			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V See fig. 3		ı	27	40	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		ı	8.0	- 1	nH		

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	30	-	ns	
Reverse recovery time See fig. 5, 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	90	-		
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 16 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	164	-		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	5.8	-	A nC A/μs	
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	8.3	-		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	260	-		
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	680	-		
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	120	-		
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	76	-		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	R SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	ı	300	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>			ı	0.83			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.50	-			
Weight			-	2.0	-	g		
vveigni			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-247AC modified (JEDEC®)	HFA16PB120H					

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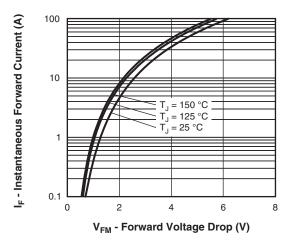


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

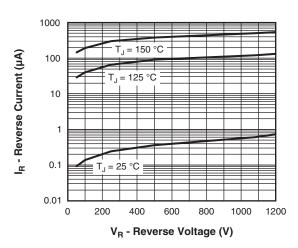


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

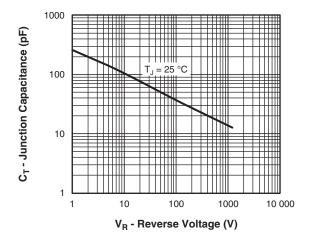


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

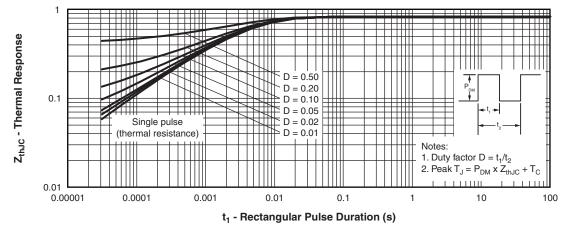


Fig. 4 - Maximum Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

Revision: 25-Sep-2019 3 Document Number: 94717 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u>





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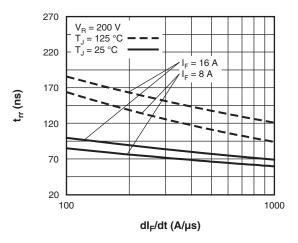


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

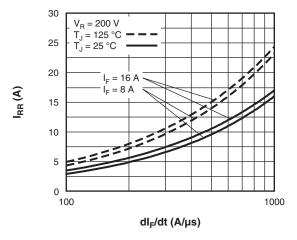


Fig. 6 - Typical Recovery Current vs.  $dI_F/dt$  (Per Leg)

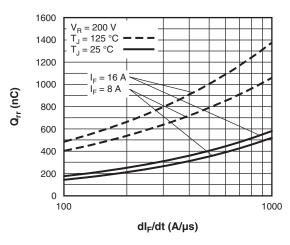


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$  (Per Leg)

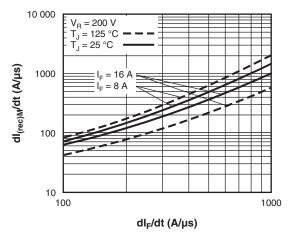
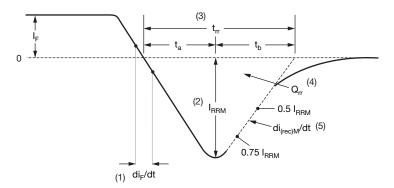


Fig. 8 - Typical dI<sub>(rec)M</sub>/dt vs. dI<sub>F</sub>/dt (Per Leg)



- di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_{rr}$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

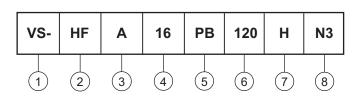
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 9 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

#### **Device code**



Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

4 - Current rating (16 = 16 A)

5 - PB = TO-247AC modified

Voltage rating: (120 = 1200 V)

7 - H = AEC-Q101 qualified

8 - Environmental digit:

N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

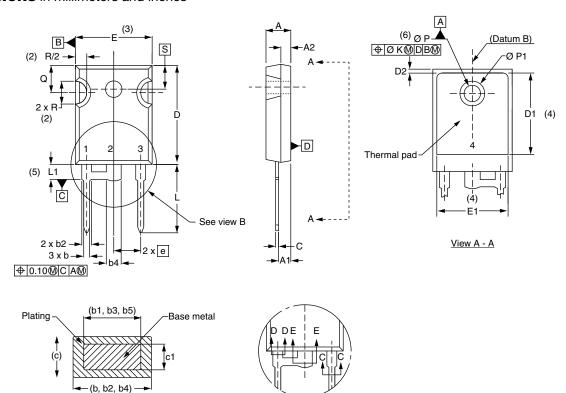
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA16PB120HN3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95253					
Part marking information	www.vishay.com/doc?95442					
SPICE model	www.vishay.com/doc?95672					

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### **TO-247AC** modified

#### **DIMENSIONS** in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

Section C - C, D - D, E - E

SYMBOL	MILLIMETERS		INC	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.530	-	
е	5.46	BSC	0.215	BSC	
Ø K 0.25		254	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	1	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

#### Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- $\ensuremath{^{(7)}}$  Outline conforms to JEDEC  $\ensuremath{^{\tiny (9)}}$  outline TO-247 with exception of dimension c

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